

# SLCS-10 - Program

The registration desk will be open on Wednesday (July 24) at Kazimierzowski Palace (16:00-20:00) and on July 25 (8:00-17:00) and July 26-27 (9:00-15:00) at the Faculty of Physics

## Wednesday, July 24

Place: Main Campus of the Warsaw University, 26/28 Krakowskie Przedmiescie Street  
Kazimierzowski Palace (Rectors building)

16:00-20:00	Registration
18:30-20:30	Welcoming glass of wine

## Thursday, July 25

Place: Faculty of Physics, 69 Hoza Street

8:00 -	Registration
8:50 - 9:00	Opening
9:00 - 9:40	<b>ThI-1 INVITED:</b> The Origin of Co Existence of Optical Transparency with Electrical Conductivity: The case of n-ZnO and n-SnO <sub>2</sub> <i>A. Zunger</i>
9:40 - 10:20	<b>ThI-2 INVITED:</b> Si donors in AlGaN alloys <i>M.S. Brandt, M.W. Bayerl, S.T.B. Goennenwein, R. Zeisel, and M. Stutzmann</i>
10:20 - 12:00	<b>Posters and coffee</b>
12:00 - 12:20	<b>ThO-1:</b> Optical identification of impurity levels in Phosphorus-doped wide-gap II-VI bulk semimagnetic semiconductors <i>Le Van Khoi, J.Kossut, R.R.Galazka</i>
12:20 - 12:40	<b>ThO-2:</b> Mixing of impurity levels by an interface electric field in CdMgTe/CdZnTe heterostructure <i>J.Lusakowski, G.Cywinski and J.Kossut</i>
12:40 - 13:00	<b>ThO-3:</b> Residual Donors in Wurtzite GaN Homoepitaxial Layers and Heterostructures. <i>G.Neu, M.Teisseire-Doninelli, C.Morhain, B.Beaumont, E.Frayssinet, M.L.Sadowski, W.Knap, A.M.Witowski, M.Leszczynski and P.Prystawko</i>
13:00 - 14:30	<b>LUNCH</b>
14:30 - 15:10	<b>ThI-3 INVITED:</b> Development of Alternative Co-doping Method of Mg and Si in GaN <i>S. Iwai, H. Hirayama, Y. Aoyagi</i>
15:10 - 15:30	<b>ThO-4:</b> Optical Properties of Si, Ge and Sn- DOPED GaN <i>A.Shikanai, H.Fukahori, Y.Kawakami, T.Mitani, T.Mukai, and Sg.Fujita</i>
15:30 - 15:50	<b>ThO-5:</b> Dynamics of Trapping on Donors and Relaxation of the B-exciton in GaN <i>K.P.Korona, A.Wysmolek, R.Stepniewski, M.Potemski, J.Kuhl, J.M.Baranowski, G.Martinez, I.Grzegory, S.Porowski</i>
15:50 - 16:10	<b>Coffee break</b>
16:10 - 16:50	<b>ThI-4 INVITED:</b> "Some like it shallower" - p-type doping in SiC <i>Peter Deak</i>
16:50 - 17:10	<b>ThO-6:</b> Nitrogen Dopants and the Z1/Z2 Defects in 4H-SiC <i>T.A.G.Eberlein, R.Jones, J.P.Goss, and P.R.Briddon</i>
17:10 - 17:30	<b>ThO-7:</b> Picosecond Time-Resolved Studies of the Excited State Lifetime of Be Acceptors in GaAs/AlGaAs Quantum Wells <i>W.-M.Zheng, M.P.Halsall, P.Harrison, J.-P R.Wells, I.V.Bradley and M.J.Steer</i>
17:30 - 17:50	<b>ThO-8:</b> Extended Theory for Local-Phonon-Coupled Low-Energy Anharmonic Excitation of Oxygen in Silicon <i>H.Yamada-Kaneta</i>

## Friday, July 26

Place: Faculty of Physics, 69 Hoza Street

9:00 - 9:40	<b>FrI-1 INVITED:</b> Kinetics of Thermal Double Donor Formation in Hydrogenated Cz-Si <i>L.I.Murin, V.P.Markevich, J.L.Lindström, T.Hallberg</i>
9:40 - 10:20	<b>FrI-2 INVITED:</b> X-Ray Evidence of Impurity Atoms Self-Organization in Heavily Doped Annealed GaAs:Te <i>T.Slupinski, E.Zielinska-Rohozinska</i>
10:20 - 12:00	<b>Posters and coffee</b>
12:00 - 12:20	<b>FrO-1:</b> Far-Infrared Spectroscopy of Shallow Acceptors in Semiinsulating GaAs: Evidence for Defect Interactions With EL2 <i>H.Ch.Alt, Y.Gomeniuk and U.Kretzer</i>
12:20 - 12:40	<b>FrO-2:</b> Shallow Thermal Donors in Heat-Treated Czochralski Grown Silicon <i>V.V.Emtsev Jr., C.A.J.Ammerlaan, V.V.Emtsev, G.A.Oganesyan, B.A.Andreev, D.I.Kuritsyn, A.Misiuk, B.Surma, C.A.Londos</i>
12:40 - 13:00	<b>FrO-3:</b> Study of IR Absorption and Photoconductivity Spectra of Thermal Double Donors in Silicon <i>B.A.Andreev, V.V.Emtsev, D.I.Kryzhkov, D.I.Kuritsyn, and V.B.Shmagin</i>
13:00 - 14:30	<b>LUNCH</b>
14:30 - 15:10	<b>FrI-3 INVITED:</b> Peculiarities of Conductivity via Impurities in Low Doped Uncompensated Silicon <i>A.P.Melnikov</i>
15:10 - 15:50	<b>FrI-4 INVITED:</b> Optically Pumped THz Semiconductor Bulk Lasers <i>S.G. Pavlov, H.-W.Hübers, V.N.Shastin, R.Kh. Zhukavin, E.E.Orlova, H.Riemann, and H.Nakata</i>
15:50 - 16:10	<b>Coffee break</b>
16:10-16:30	<b>FrO-4:</b> THz Lasing of SiGe/Si Quantum-Well Structures Due to Shallow Acceptors <i>I.V.Altukhov, E.G.Chirkova, V.P.Sinis, M.S.Kagan, R.T.Troeger, S.K.Ray, J.Kolodzey</i>
16:30-16:50	<b>FrO-5:</b> Impurity Pairs and Relaxation of Excitation in Silicon Doped with III and V Group Impurities <i>Ya.E.Pokrovskii and N.A.Khvalkovskii</i>
16:50-17:10	<b>FrO-6:</b> On the Impurity Photoconductivity of Uniaxially Stressed p-Ge <i>V.Ya.Aleshkin, A.V.Gavrilenko, V.I.Gavrilenko, D.V.Kozlov, A.T.Dalakjan, V.N.Tulupenko</i>
19:00	<b>Conference Dinner - Bistrot Restaurant, 12 Foksal Street</b>

## Saturday, July 27

Place: Faculty of Physics, 69 Hoza Street

9:00 - 9:40	<b>SaI-1 INVITED: Hydrogen as a Shallow Center in Semiconductors</b> <i>C.G. Van de Walle</i>
9:40 - 10:00	<b>SaO-1:</b> Hydrogen and Muon States in II-VI Semiconductor Compounds <i>A.Weidinger, H.V.Alberto, J.M.Gil, R.C.Vilao, J.Pioto Duarte, N.Ayres de Campos, S.F.J.Cox, S.P.Cottrell, P.J.C.King, J.S.Lord, E.A.Davis</i>
10:00 - 10:20	<b>SaO-2:</b> Hydrogen Passivation of the SiGa DONOR in GaP <i>W.Ulrici, B.Clerjaud, D.Côte</i>
10:20 - 12:00	<b>Posters and coffee</b>
12:00 - 12:20	<b>SaO-3:</b> The Electrical Activity of Shallow Hydrogen Centres in Carbon Rich Silicon <i>B.Hourahine, R.Jones, O.Andersen, L.Dobaczewski, A.R.Peaker, K.Bonde Nielsen, P.R.Briddon, S.Öberg</i>
12:20 - 12:40	<b>SaO-4:</b> Shallow Donor Activity of S-H, Se-H and Te-H Complexes in Silicon <i>J.Coutinho, V.J.B.Torres, A.Resende, R.Jones, P.R.Briddon</i>
12:40 - 13:00	<b>SaO-5:</b> Coulomb Related Landau Spectra of Axial and Double Acceptors in Germanium <i>P.Fisher, R.E.M.Vickers, K.Ishida</i>
13:00 - 14:30	<b>LUNCH</b>
14:30 - 15:10	<b>SaI-2 INVITED: Photoluminescence Studies on Isotopically Purified Silicon</b> <i>D.Karaiskaj, M.L.W.Thewalt, T.Ruf, M.Cardona</i>
15:10 - 15:50	<b>SaI-3 INVITED: Selective Magneto-luminescence Spectroscopy of Donor-acceptor Pairs in n-GaAs</b> <i>A. Wysmolek</i>
15:50 - 16:10	<b>Coffee break</b>
16:10 - 16:30	<b>SaO-6:</b> Anomalous PL Brightening Caused by Impact Formation of D <sup>+</sup> ,X Complex During Impact Ionization Avalanche in n-GaAs <i>Kazuori Aoki</i>
16:30 - 16:50	<b>SaO-7:</b> MOCVD n-InAs Thin Layers Compared with MBE Samples - Far Infrared Magnetophotoconductivity <i>Z.Romanowski, M.Szot, K.Karpierz, R.Bozek, R.Stepniewski and M.Grynberg</i>
16:50 -	<b>Closing address</b>

## Poster Session, Thursday - July 25

ThP-01	A. Blom, M. A. Odnoblyudov, I. N. Yassievich and K.-A. Chao	RESONANT DONOR STATES IN DOPED QUANTUM WELLS
ThP-02	A. Latgé, M. Pacheco, and Z. Barticevic	ELECTRIC FIELD EFFECTS on INTRADONOR MAGNETO-TRANSITIONS in QUANTUM-WELL STRUCTURES
ThP-03	S. Y. López, N. Porrás-Montenegro, and C. A. Duque	EFFECTS OF THE HYDROSTATIC STRESS ON THE DENSITY OF IMPURITY STATES AND DONOR RELATED OPTICAL ABSORPTION SPECTRA IN GaAs-(Ga,Al)As QUANTUM WELLS
ThP-04	A. León, M. Pacheco, and Z. Barticevic	FAR-INFRARED SPECTRUM of DONOR IMPURITIES in QUANTUM DOTS in MAGNETIC FIELDS
ThP-05	A.A. Avetisyan, A.P. Djotyan and E.M. Kazaryan	EXCITON - DONOR COMPLEXES IN A SEMICONDUCTOR QD
ThP-06	A.L. Morales, A. Montes, S.Y. López, N. Raigoza, and C.A. Duque	DONOR-RELATED DENSITY OF STATES AND POLARIZABILITY IN A GaAs-(Ga,Al)As QUANTUM-WELL UNDER HYDROSTATIC PRESSURE AND APPLIED ELECTRIC FIELD
ThP-07	Arshak L. Vartanian	THE EFFECT OF ELECTRON-PHONON INTERACTION ON THE SHALLOW IMPURITY BINDING ENERGY IN QUANTUM WIRES IN THE PRESENCE OF A MAGNETIC FIELD
ThP-08	B. S. Monozon and P. Schmelcher	EFFECTS OF AN ELECTRIC AND STRONG MAGNETIC FIELDS ON THE D - CENTRE IN A QUANTUM WELL
ThP-09	D.V. Gulyaev, A.M. Gilinsky, A.I. Toropov, A.K. Bakarov, and K.S. Zhuravlev	RECOMBINATION of EXCITONS BOUND on DONOR-ACCEPTOR IMPURITY PAIRS in d-DOPED TYPE II GaAs/AlAs SUPERLATTICES
ThP-10	I. D. Mikhailov, F. J. Betancur, R. A. Escorcía and J. Sierra-Ortega	STABILITY of D- GROUND STATE in QUANTUM WELLS under STRONG MAGNETIC FIELDS
ThP-11	J.H. Marín, J. Sierra-Ortega, R.A. Escorcía, F.J. Betancur and I.D. Mikhailov	OFF-CENTER DONORS in SPHERICAL QUANTUM DOTS
ThP-12	M. de Dios-Leyva, O. Fernandez-Gómez, E. Reyes-Gómez, and L.E. Oliveira	ON the VIRIAL THEOREM VALUE and SCALING of COULOMB-BOUND STATES in SEMICONDUCTOR HETEROSTRUCTURES: EFFECTS of MAGNETIC FIELDS
ThP-13	M. Szot, K. Karpierz, J. Kossut and M. Grynberg	FIR PHOTON ENERGY INDEPENDENT INTRA-IMPURITY TRANSITIONS in UNIFORMLY IODINE DOPED CdTe/Cd <sub>x</sub> Mg <sub>1-x</sub> Te QUANTUM WELL
ThP-14	N.A. Bekin, R.Kh. Zhukavin, L.V. Krasilnikova, S.G. Pavlov, V.N. Shastin	LOCALIZED AND RESONANT SHALLOW DONOR STATES IN GaAs/InGaAs DOUBLE-QUANTUM-WELL HETEROSTRUCTURES
ThP-15	V.Ya. Aleshkin, V.I. Gavrilenko, D.V. Kozlov	SHALLOW ACCEPTORS in Si/SiGe QUANTUM WELL HETEROSTRUCTURES
ThP-16	A. A. Belov, F. Firszt, V. S. Gorelik, A. L. Karuzskii, E. I. Mahov, H. Meczynska, A.V. Perestoronin, P. P. Sverbil, J. Szatkowski	ANTI-STOKES LUMINESCENCE IN TERNARY ZnMgSe COMPOUNDS AT LIQUID HELIUM TEMPERATURE
ThP-17	A. N. Avdonin, G. N. Ivanova, D. D. Nedeoglo, N. D. Nedeoglo, V. P. Sirkeli	ELECTRICAL AND LUMINESCENCE PROPERTIES OF ZnSe SINGLE CRYSTALS DOPED WITH SHALLOW DONOR IMPURITY
ThP-18	K. Lott, O. Volobujeva, A. Öpik, T. Nirk, L. Türn and M. Noges	HIGH TEMPERATURE ELECTRICAL CONDUCTIVITY in DONOR-DOPED II-VI COMPOUNDS
ThP-19	K. Lott, O. Volobujeva, M. Raukas, L. Türn, A. Grebennik and A. Vishnjakov	INVESTIGATION of EXCESS Zn in ZnO
ThP-20	K. Yoshino, T. Hata, H. Komaki, Y. Akaki and T. Ikari	ELECTRICAL and OPTICAL CHARACTERIZATION of n-TYPE ZnO THIN FILMS
ThP-21	Kenji Yoshino, Minoru Yoneta, Atsutoshi Arakawa, Kenzo Ohmori, Hiroshi Saito and Masakazu Ohishi	IMPURITY LEVELS of HIGH QUALITY p-DOPED ZnTe SINGLE CRYSTAL
ThP-22	M. Yoneta, H. Kato, K. Yoshino, M. Ohishi, H. Saito, K. Ohmori	CHEMICAL ETCHING-INDUCED DEFECTS in n-TYPE ZnSe CRYSTAL GROWN by PHYSICAL VAPOR TRANSPORT
ThP-23	A.L. Gurskii, M. Germain, S.V. Voitkov, E.V. Lutsenko, I.P. Marko, V.N. Pavlovskii,	EFFECT OF ELECTRON-LO-PHONON COUPLING AND CHEMICAL SHIFT ON RECOMBINATION VIA SHALLOW

	B. Schineller, M. Heuken, E. Kartheuser, G.P. Yablonskii	IMPURITIES IN WIDE BAND-GAP II-VI AND III-V SEMICONDUCTORS
ThP-24	A.Wysmolek, M.Potemski, R.Stepniewski, J.M.Baranowski, R. L. Jones, D.C.Look, S. S. Park, and K.Y.Lee	RESONANT INTERACTION of LO PHONONS with EXCITED DONOR STATES in GaN
ThP-24	J. H. Kim, I.-W. Park, S. H. Choh, S. S. Park, B. G. Kim, and Y. H. Kang	PARAMAGNETIC DEFECTS in NEUTRON IRRADIATED BULK GaN CRYSTALS
ThP-26	K. P. Korona, M. Palczewska, R. Doradziński, M. Pietras, M. Kamińska, J. Kuhl	PROPERTIES of ZINC ACCEPTOR and EXCITON BOUND to ZINC STUDIED in AMMONOTHERMAL GaN
ThP-27	V.V. Emtsev, V.Yu. Davydov, D.S. Poloskin, G.A. Oganessian, N.M. Shmidt, A.S. Usikov, and V.V. Kozlovskii	SHALLOW DONOR CENTRES in GALLIUM NITRIDE
ThP-28	S.B. Mikhrin and K.F. Shtel'makh	EPR of SHALLOW DONORS in InP:Ce

## Poster Session, Friday – July 26

FrP-01	Hirromichi Nagao and Takao Wada	ALGORITHM ANIMATION SYSTEM for SUPERDIFFUSION in SEMICONDUCTORS USING COMPUTER GRAPHICS
FrP-02	I.V. Antonova, S.A. Smagulova	FORMATION of the SHALLOW DONORS and ACCEPTORS in SILICON IRRADIATED with EITHER ELECTRON or HIGH ENERGY IONS and ANNEALED at TEMPERATURES 400-700°C
FrP-03	L.I. Khirunencko, V. Kobzar, Yu.V. Pomozov, M.G. Sosnin, V.P. Markevich, L.I. Murin, and A.R. Peaker	DEFECT-IMPURITY INTERACTIONS in IRRADIATED TIN-DOPED Cz-Si CRYSTALS
FrP-04	M. Kaniewska, I. V. Antonova, and V. P. Popov	STUDY of COMPLEX CARRIER PROFILES in HYDROGEN IMPLANTED and ANNEALED SILICON
FrP-05	N. Pinho, J. Coutinho, R. Jones P.R. Briddon	SHALLOW RELATED LEVELS of the SELF-INTERSTITIAL TRAPPED by OXYGEN in SILICON
FrP-06	S.I. Budzulyak, Yu.P. Dotsenko, V.M. Ermakov, V.V. Kolomoets, B.B. Suss, E.F. Venger and V.I. Khivrich	THERMODYNAMIC ACTIVATION ENERGY in TRANSMUTATION DOPED N-Si(P)
FrP-07	Xu Jin, Deren Yang, Chunlong Li, Xiangyang Ma, Duanlin Que, and A. Misiuk	THERMAL DONORS in NITROGEN-DOPED SILICON ANNEALED at 450 °C under HIGH PRESSURE of 1GPa
FrP-08	Y. Ohmura, M. Suzuki, M. Takahashi, A. Emura, N. Sakamoto, T. Meguro and Y. Yamamoto	n-TYPE (P, Sb) and p-TYPE (B) DOPING of HYDROGENATED AMORPHOUS Si by REACTIVE RF CO-SPUTTERING
FrP-09	Y.X. Li, M.X. Pan, T.J. Liu, Q.Y. Hao, C.C. Liu, Y.S. Xu, D.R. Yang and D.L. Que	DEPTH PROFILES of THERMAL DONORS in NTD-CZ-Si
FrP-10	H. Komaki, K. Yoshino, M. Yoneta, Y. Akaki and T. Ikari	CHARACTERIZATION of Sb-DOPED p-TYPE CuInS <sub>2</sub> CRYSTALS
FrP-11	Leonid I. Skatkov	CHANGE in the CONCENTRATION of SHALLOW -LEVEL CENTERS in Nb <sub>2</sub> O <sub>5</sub> SEMICONDUCTOR FILMS CAUSED by GENERATING ANION DEFECTS on their SURFACE
FrP-12	Shosuke MOCHIZUKI and Fumito FUJISHIRO	SHALLOW- and DEEP-EXCITED STATES of MESOSCOPIC STRUCTURE in AgI-gAl <sub>2</sub> O <sub>3</sub> COMPOSITES
FrP-13	Shosuke MOCHIZUKI and Fumito FUJISHIRO	SHALLOW- and DEEP-LUMINESCENCE CENTERS in AgI-BASED SUPERIONIC CONDUCTOR GLASS
FrP-14	I.N. Yassievich, M.A. Odnoblyudov, A.A. Prokofiev, V.M. Chistyakov, and K.A. Chao	ACCEPTOR RESONANT STATES and THz LASING in STRAINED SEMICONDUCTORS and SEMICONDUCTOR NANOSTRUCTURES
FrP-15	J.L. Nie, L.B. Lin and W. Xu	HYDROGEN-LIKE IMPURITIES in SEMICONDUCTORS in INTENSE TERAHERTZ LASER FIELDS
FrP-16	N. A. Bekin, R. Kh. Zhukavin, L. V. Krasilnikova, V. N. Shastin, B. N. Zvonkov	THz RADIATION FROM OPTICALLY PUMPED N-TYPE GaAs/InGaAs MULTI QUANTUM WELL HETEROSTRUCTURES
FrP-17	S.G. Pavlov	ELECTRICALLY PUMPED FAR-INFRARED POPULATION INVERSION IN HETEROSTRUCTURES DOPED BY SHALLOW IMPURITY CENTRES
FrP-18	L.T. Ho	SINGLY IONIZED MAGNESIUM-OXYGEN COMPLEX IMPURITIES in SILICON
FrP-19	Nakanishi, N. Fukata and M. Suezawa	COMPLEXES of POINT DEFECTS and IMPURITIES in ELECTRON-IRRADIATED n-TYPE Cz-Si PRE-DOPED with HYDROGEN
FrP-20	Y. Kamiura, K. Fukuda, Y. Iwagami, T. Fukuda, T. Ishiyama, and Y. Yamashita	STUDY of the ELECTRONIC STATE and Structure Related to a PLATINUM-DIHYDROGEN COMPLEX in Si and CHARGE-STATE-DEPENDENT CAGE MOTION of HYDROGEN in the COMPLEX
FrP-21	M. Kravtsiv, O. Shpotyuk, A. Kovalskiy	ON the PROBLEM of TRAPPING CENTERS FORMATION in ORGANIC POLYCYCLIC COMPOUNDS

## Poster Session, Saturday - July 27

SaP-01	A. Nouiri, Y. Sayad, and A. Djemel	STUDY OF ACCEPTOR CENTERS IN GaAs AFTER HIGH TEMPERATURE ANNEALING. EXPERIMENTS AND CALCULATION.
SaP-02	M.A. Chernikov, O.A. Ryabushkin	ACCEPTOR STATES DETECTION by MICROWAVE and CURRENT MODULATION SPECTROSCOPY.
SaP-03	A.E. Nickolaenko, A.M. Gilinsky, O.A. Shegai, T.S. Shamirzaev, and K.S. Zhuravlev	OPTICALLY DETECTED MAGNETIC RESONANCE OF SHALLOW DONORS IN GaAs OBSERVED IN PHOTOLUMINESCENCE KINETICS
SaP-04	E.P.Skipetrov, E.A.Zvereva, N.A.Chernova, L.A.Skipetrova, B.B.Kovalev, O.S.Volkova, A.V.Golubev, E.I.Slyn'ko	IMPURITY RELATED MAGNETISM IN THE DILUTED MAGNETIC SEMICONDUCTORS Pb <sub>1-x</sub> Sn <sub>x</sub> Te:Yb.
SaP-05	N. Romèeviaè, D.R. Khokhlov, D. Stojanoviaè, M. Romèeviaè and A. V. Nikorich	DX-LIKE CENTERS and PERSISTENT PHOTOCONDUCTIVITY EFFECT in INDIUM DOPED PbTe BASED ALLOYS
SaP-06	Yong-Sung Kim and K. J. Chang	NITROGEN-HYDROGEN COMPLEXES in GaAs and GaAs <sub>1-x</sub> N <sub>x</sub> ALLOYS
SaP-07	T.S. Shamirzaev, K.S. Zhuravlev, J. Bak-Misiuk, A. Misiuk, J.Z. Domagala, J Adamczewska, V.V. Preobrazhenskii	STRESS INDUCED TRANSFORMATION IN PHOTOLUMINESCENCE SPECTRA OF HOMOEPITAXIAL BERYLLIUM - DOPED GaAs THIN FILMS
SaP-08	Takao Wada and Hiroshi Fujimoto	IDENTIFICATION of SUPERDIFFUSION of IMPURITY ATOMS in DAMAGE-FREE REGIONS of SEMICONDUCTORS
SaP-09	Takao Wada and Hiroshi Fujimoto	ELECTRON BEAM DOPING of IMPURITY ATOMS into SEMICONDUCTORS by SUPERDIFFUSION
SaP-10	V.P. Markevich, V.V. Litvinov, L. Dobaczewski, L.J. Lindström, L.I. Murine, and A.R.Peaker	RADIATION-INDUCED DEFECTS and THEIR TRANSFORMATIONS in OXYGEN-RICH GERMANIUM CRYSTALS
SaP-11	W. Gehlhoff , D. Azamat, A. Hoffman, and N. Dietz	DONOR CENTRES in ZINC GERMANIUM DIPHOSPHIDE PRODUCED by ELECTRON IRRADIATION
SaP-12	B.N. Zaverukhin, N.N. Zaverukhina, E.B Zaverukhina	IONIZATION of SHALLOW IMPURITY CENTERS by ULTRASONIC WAVE in SEMICONDUCTORS
SaP-13	Kh. O. Ibragimov, N. S. Abakarova and K. M. Aliev	INSTABILITY of a CURRENT in p-GE with DEEP-LEVELS of Au
SaP-14	N.T. Bagraev, A.D. Bouravleuv, W. Gehlhoff, L.E. Klyachkin, A.M. Malyarenko	ELECTRON-DIPOLE RESONANCE of IMPURITY CENTRES EMBEDDED in SILICON MICROCAVITIES
SaP-15	O.Shpotyuk, J.Filipecki, A.Kozdras, A.Kovalskiy	COORDINATION POSITRON-TRAPPING CENTERS IN VITREOUS CHALCOGENIDE SEMICONDUCTORS
SaP-16	R. Mota, M. Machado and P. Piquini	ELECTRONIC and STRUCTURAL PROPERTIES of BN NANOCONES
SaP-17	S.A. Omelchenko, Yu.A. Gulevski, V.I. Klimenko, M.F. Bulanyi, S.Z. Shmurak	IRREVERSIBLE TRANSFORMING of SHALLOW CENTRES in ELECTRIC FIELDS of DISLOCATIONS